TOSHIBA TRANSISTOR SILICON PNP EPITAXIAL TYPE (PCT PROCESS)

2 S A 9 6 5

POWER AMPLIFIER APPLICATIONS

DRIVER STAGE AMPLIFIER APPLICATIONS

Complementary to 2SC2235.

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	v_{CBO}	-120	V
Collector-Emitter Voltage	v_{CEO}	-120	V
Emitter-Base Voltage	$v_{ m EBO}$	-5	V
Collector Current	$I_{\mathbf{C}}$	-800	mA
Emitter Current	${f I_E}$	800	mA
Collector Power Dissipation	$P_{\mathbf{C}}$	900	mW
Junction Temperature	${f T_j}$	150	°C
Storage Temperature Range	${ m T_{stg}}$	-55~150	°C

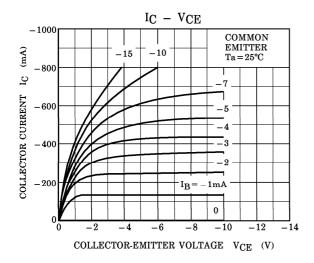
Unit in mm 5.1 MAX 0.75MAX. 1.0MAX. <u>XAM8.0</u> 0.6MAX 1. EMITTER 2. COLLECTOR 3. BASE **JEDEC** TO-92MOD JEITA **TOSHIBA** 2-5J1A

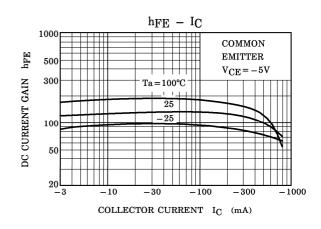
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

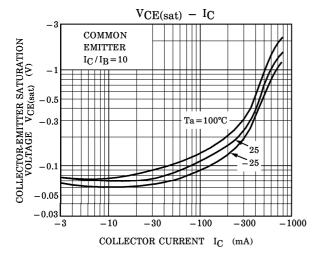
ELECTRICAL CHARACTERISTICS (Ta = 25°C)		Wei	Veight: 0.36g (Typ.)			
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = -120V, I_E = 0$	_	1	-100	nA
Emitter Cut-off Current	$I_{ m EBO}$	$V_{EB} = -5V, I_C = 0$	_	ı	-100	nA
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	$I_{\rm C} = -10 {\rm mA}, \ I_{\rm B} = 0$	-120	I	_	V
Emitter -Base Breakdown Voltage	V _{(BR)EBO}	$I_{E} = -1 \text{mA}, I_{C} = 0$	-5	1	_	V
DC Current Gain	h _{FE} (Note)	$V_{CE} = -5V, I_{C} = -100 \text{mA}$	80	I	240	
Collector-Emitter Saturation Voltage	V _{CE(sat)}	$I_C = -500 \text{mA}, I_B = -50 \text{mA}$	_	_	-1.0	V
Base-Emitter Voltage	$ m V_{BE}$	$V_{CE} = -5V, I_{C} = -500 \text{mA}$	_		-1.0	V
Transition Frequency	${f f_T}$	$V_{CE} = -5V, I_{C} = -100 \text{mA}$	_	120	_	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$	_	_	40	pF

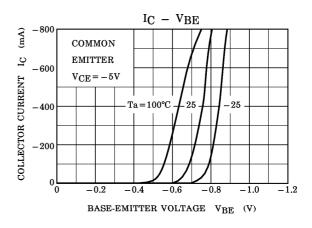
(Note): h_{FE} Classification $O: 80\sim160, Y: 120\sim240$

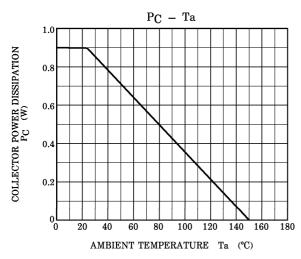
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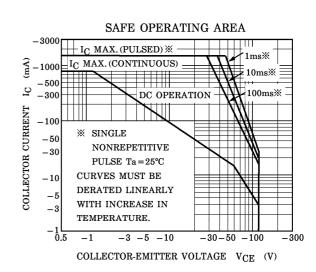












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